Mott-Hubbard and Anderson Metal-Insulator Transitions in Correlated and Disordered Electronic Systems

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Main goal:

Some random events are better classified by means that are different than the arithmetic average

Main result:

Zero-temperature phase diagram of the disordered Hubbard model at half filling



Collaboration:

- Walter Hofstetter Harvard University, USA
- Dieter Vollhardt Augsburg University, Germany

Plan of the talk:

- 1. Introduction
 - Mott-Hubbard and Anderson metal-insulator transitions (MIT)
 - Anderson-Hubbard Hamiltonian
 - Description of Anderson localization
 - Widely distributed random quantities
 - Arithmetic vs. geometric means
 - Log-normal distribution
- 2. Modification within DMFT to include Anderson localization
- 3. Phase diagram and MITs in details
- 4. Conclusions

Mott-Hubbard MIT at n = 1:

$$H = \epsilon_0 \sum_{i\sigma} n_{i\sigma} + \sum_{ij\sigma} t_{ij} a_{i\sigma}^{\dagger} a_{j\sigma} + U \sum_i n_{i\uparrow} n_{i\downarrow}$$





DMET cooperie

Anderson MIT:

$$H = \sum_{i\sigma} \epsilon_i n_{i\sigma} + \sum_{ij\sigma} t_{ij} a_{i\sigma}^{\dagger} a_{j\sigma}$$

Probability distribution function

$$\mathcal{P}(\boldsymbol{\epsilon}_i) = \frac{1}{\Delta} \Theta\left(\frac{\Delta}{2} - |\boldsymbol{\epsilon}_i|\right)$$



Returning probability $P_{j \to j}(t \to \infty; V \to \infty)$?



 $P_{j \to j}(t \to \infty; V \to \infty) = 0$ for extended states

 $P_{j \to j}(t \to \infty; V \to \infty) > 0$ for localized states

Anderson, PR 109, 1492 (1958) - At strong disorder the nature of electronic states at a given energy changes from extended to exponentially localized

Accumulation of quantum interference corrections affects the transport

According to one-parameter scaling theory [g = g(L)] (noninteracting system)

- If dim = 1 or 2 all states are localized
- If dim=3 there is a critical disorder above which the states are localized

Abrahams et al., PRL 42, 673 (1979)



Which quantity characterizes Anderson MIT?

- 1. Decaying of wavefunction $|\Psi_n(r_i)| \sim e^{-|r-r_i|/\xi(E_n)|}$
 - metal $\xi \to \infty$
 - insulator $\xi < \infty$
- 2. Inverse participation ratio P^{-1} [inverse number of sites that contribute to $\Psi_n(r_i)$]
 - metal $P^{-1} \sim 1/N$
 - insulator $P^{-1} \sim \text{const}$
- 3. Conductance G
 - metal G > 0
 - insulator G = 0
- 4. Local Density of States (LDOS)

$$\rho_i(E) = \sum_{n=1}^N |\Psi_n(r_i)|^2 \delta(E - E_n)$$

To match the Anderson localization theory with DMFT (strong correlations) the most useful is to use LDOS

Why LDOS?

Heuristic arguments:

$$P_{j \to j}(t) = |G_j(t)|^2$$

$$G_j(t) \sim e^{i(\epsilon_j + \Sigma'_j)t - |\Sigma''_j|t} \sim e^{-\frac{t}{\tau_{\text{esc}}}}$$



 $\rho_j(E)$ is different at different $R_j!$ Random quantity!

Statistical description $P[\rho_j(E)]!$



Schubert et al. cond-mat/0309015

Broadly distributed $P[\rho_j(E_F)]$

Log-normal distribution - tutorial:

$$f(x) = \frac{1}{\sqrt{2\pi\sigma^2}} \frac{1}{x} e^{-\frac{(\ln x - \mu)^2}{2\sigma^2}}$$

- It has both long tail and all moments
- Typical value $x_{typ} = e^{\mu \sigma^2}$
- Median $x^{med} = e^{\mu}$
- Arithmetic mean $\langle x \rangle = e^{\mu + \frac{\sigma^2}{2}}$
- Geometric mean $x_{geom} = e^{\langle \ln x \rangle} = e^{\mu}$



Log-normal distribution - cont.:

Log-normal distribution serves as a prototype distribution which is characterized by infinitely many moments

F. Galton 1879; D. McAlister 1879

How to get log-normal?

- $x = e^y$
- $x_n = \prod_{i=1}^n y_i$ with CLT

Applications: astrophysics, physics (glass, polymers, networks), economy, sociology, biology, geology, etc.

Near Anderson localization typical LDOS is approximated by geometrical mean

 $\rho_{typ}(E) \approx \rho_{geom}(E) = e^{\langle \ln \rho_i(E) \rangle}$



Why should it work at all?

$$\rho_{geom}(E) = e^{\langle \ln \rho_i(E) \rangle} = e^{\frac{1}{\Delta} \sum_{i=1}^N \ln \rho_i(E)} = \prod_{i=1}^N \rho_i(E)^{\frac{1}{\Delta}}$$

$$\exists \ \rho_i(E) = 0 \Longrightarrow \rho_{geom}(E) = 0$$

Theorem (F.Wegner 1981):

 $\rho(E) = \langle \rho_i(E) \rangle > 0$

DMFT with Anderson MIT:

after idea from: Dobrosavljevic et al., Europhys. Lett. 62, 76 (2003)

$$H^{\text{SIAM}} = \sum_{\sigma} (\epsilon_{i} - \mu) a_{i\sigma}^{\dagger} a_{i\sigma} + U n_{i\uparrow} n_{i\downarrow}$$
$$+ \sum_{k\sigma} V_{k} a_{i\sigma}^{\dagger} c_{k\sigma} + hc + \sum_{k\sigma} \epsilon_{k} c_{k\sigma}^{\dagger} c_{k\sigma}$$
$$G(\omega, \epsilon_{i}) \rightarrow \rho_{i}(\omega) = -\frac{1}{\pi} \text{Im} G(\omega, \epsilon_{i})$$

$$\rho_g(\omega) = e^{\langle \ln \rho_i(\omega) \rangle}; \quad G(\omega) = \int d\omega' \frac{\rho_g(\omega)}{\omega - \omega'}$$

$$G^{-1}(\omega) = \omega - \eta(\omega) - \Sigma(\omega)$$

Phase diagram for disordered Hubbard model:

$$N_0(\epsilon) = \frac{2}{\pi D} \sqrt{D^2 - \epsilon^2}; \quad \eta(\omega) = \frac{D^2}{4} G(\omega)$$

T = 0, n = 1, W = 2D = 1



Mott-Hubbard transition in disordered Hubbard model:



* Friedel rule

* Hysterisis $\Delta_{c1}(U)$, $\Delta_{c2}(U)$

Spectral functions in disordered Hubbard model:

U/W=1.25

U/W=1.75



* Redistribution of spectral weight

Anderson transition in Hubbard model:



* $A(0) \sim [\Delta_c(U) - \Delta(U)]^{\beta}$

with $\beta=1 \text{ or } \beta < 1$

Conclusions:

- Geometrical means used to study Anderson MIT in correlated electron system within DMFT
- Complete phase diagram
- Hysteresis and crossover in Mott-Hubbard MIT
- Nonmonotonic behavior of $\Delta_c(U)$ at Anderson MIT
- Two insulators connected adiabatically